

MA4X160A

Silicon epitaxial planar type

For switching circuits

■ Features

- Two isolated elements contained in one package, allowing high-density mounting
- Centrosymmetrical wiring, allowing to free from the taping direction
- Short reverse recovery time t_{rr}
- Small terminal capacitance, C_t

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit	
Reverse voltage (DC)	V_R	80	V	
Repetitive peak reverse voltage	V_{RRM}	80	V	
Reverse voltage (DC)	Single	$I_{F(AV)}$	100	mA
	Double	$I_{F(AV)}$	75	mA/Unit
Repetitive peak forward current	Single	I_{FRM}	225	mA
	Double	I_{FRM}	170	mA/Unit
Non-repetitive peak forward surge current*	Single	I_{FSM}	500	mA
	Double	I_{FSM}	375	mA/Unit
Junction temperature	T_j	150	$^\circ\text{C}$	
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$	

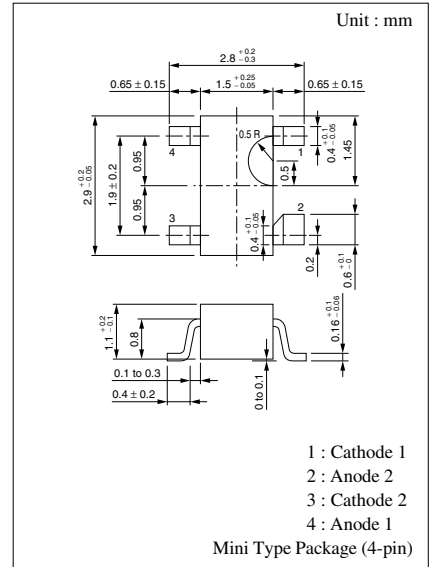
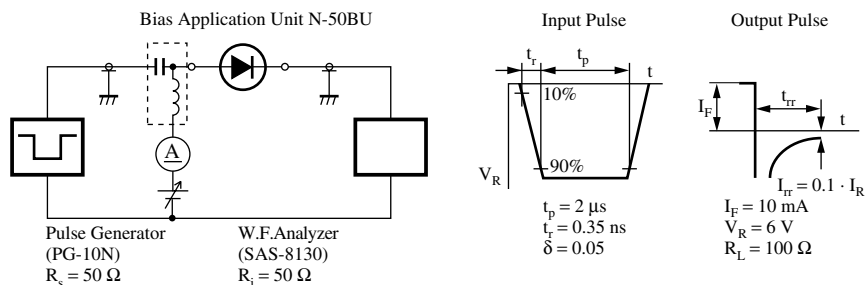
Note) * : $t = 1 \text{ s}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 75 \text{ V}$			0.1	μA
Forward voltage (DC)	V_F	$I_F = 100 \text{ mA}$		0.95	1.2	V
Reverse voltage (DC)	V_R	$I_R = 100 \mu\text{A}$	80			V
Terminal capacitance	C_t	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$		0.9	2	pF
Reverse recovery time*	t_{rr}	$I_F = 10 \text{ mA}, V_R = 6 \text{ V}$ $I_{rr} = 0.1 \cdot I_R, R_L = 100 \Omega$			3	ns

Note) 1. Rated input/output frequency: 100 MHz

2. * : t_{rr} measuring circuit



Marking Symbol: M1E

Internal Connection

